

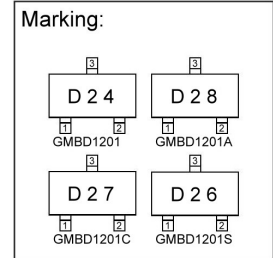
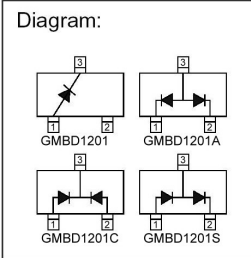
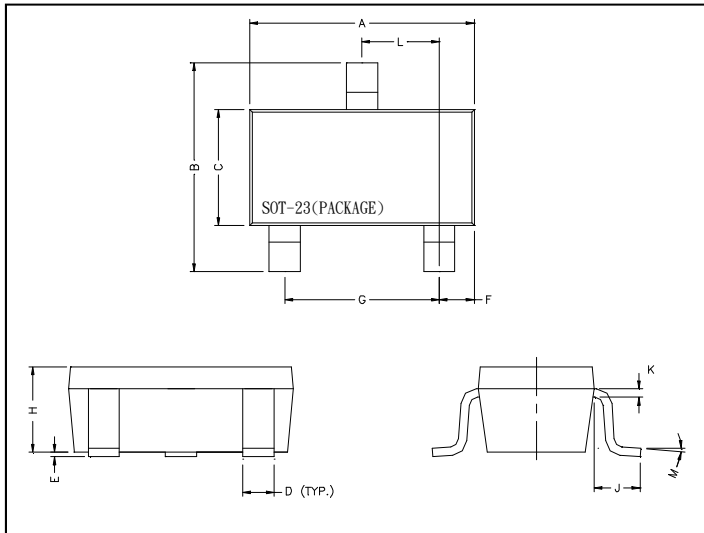
GMBD1201\A\C\S

SURFACE MOUNT, SWITCHING DIODE
VOLTAGE 100V, CURRENT 200mA

Description

The GMBD1201\A\C\S are general purpose for small signal diodes.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

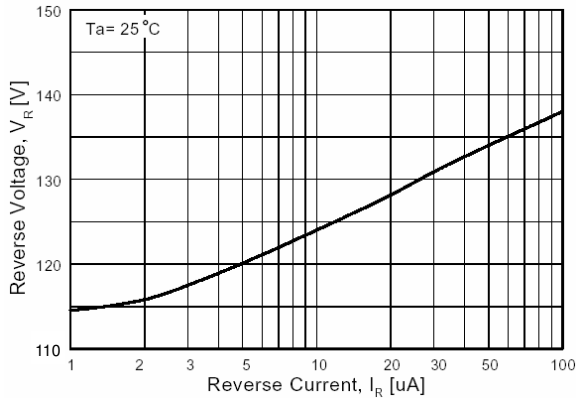
Absolute Maximum Ratings (TA = 25°C)

Parameter	Symbol	Ratings	Unit
Max. Repetitive Reverse Voltage	VRRM	100	V
Average Rectified Forward Current	IF(AV)	200	mA
Non-Repetitive Peak Forward surge Current @1s @1ms	IFSM	1 2	A
Power Dissipation	PD	350	mW
Thermal Resistance Junction to Ambient Air	RθJA	357	°C/W
Storage Temperature Range	TSTG	-55 ~ +150	°C
Operating Junction Temperature	TJ	+150	°C

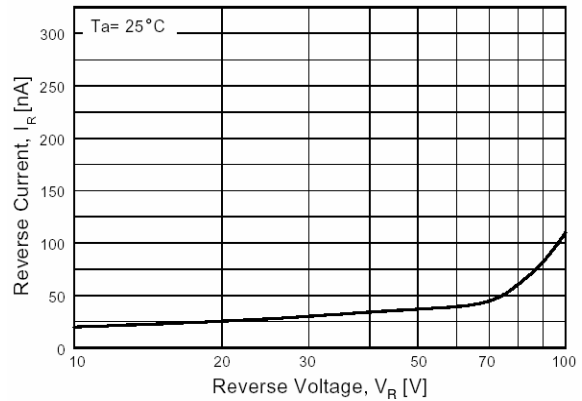
Electrical Characteristics (TA = 25°C)

Characteristics	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Breakdown Voltage	VR	100	-	-	V	IR=100uA
Forward Voltage	VF	-	700	800	mV	IF=1mA
		-	800	900	mV	IF=10mA
		-	1.1	1.2	V	IF=100mA
		-	1.2	1.3	V	IF=200mA
		-	1.3	1.4	V	IF=300mA
Reverse Current	IR	-	-	25	nA	VR=20V
		-	-	50	nA	VR=50V
		-	-	5.0	uA	VR=50V, TA=150°C
Total Capacitance	CT	-	-	2.0	pF	VR=0, f=1.0MHZ
Reverse Recovery Time	trr	-	-	4.0	ns	IF=IR=10mA, IRR=1mA, RL=100Ω

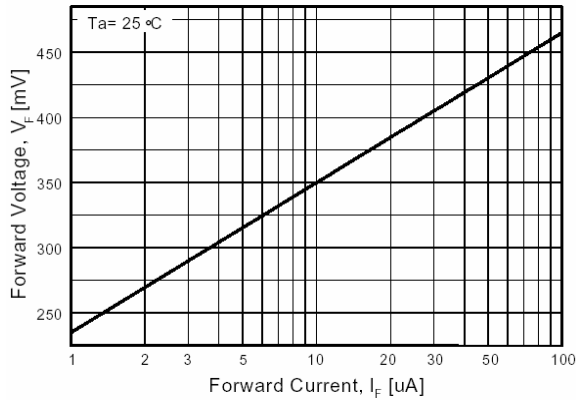
Characteristics Curve



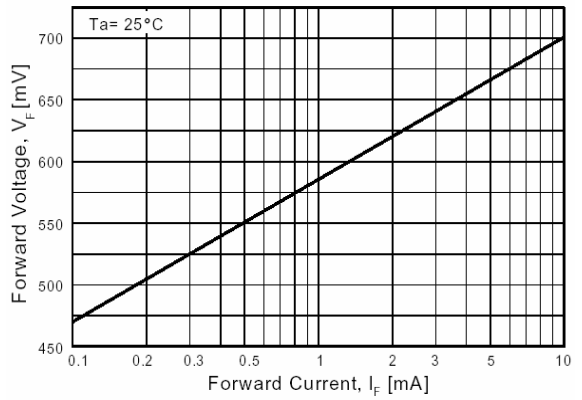
**Fig 1. Reverse Voltage vs. Reverse Current
 BV - 1.0 to 100uA**



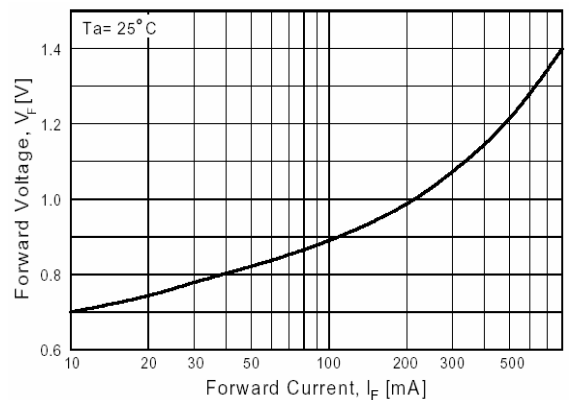
**Fig 2. Reverse Current vs. Reverse Voltage
 IR - 10 to 100V**



**Fig 3. Forward Voltage vs. Forward Current
 VF - 1.0 to 100uA**



**Fig 4. Forward Voltage vs. Forward Current
 VF - 0.1 to 10mA**



**Fig 5. Forward Voltage vs. Forward Current
 VF - 10 to 800mA**

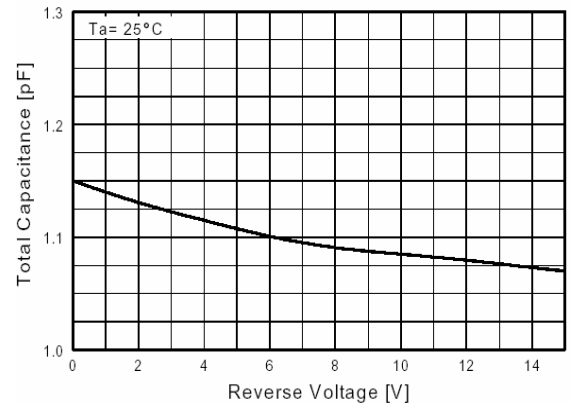


Fig 6. Total Capacitance vs. Reverse Voltage

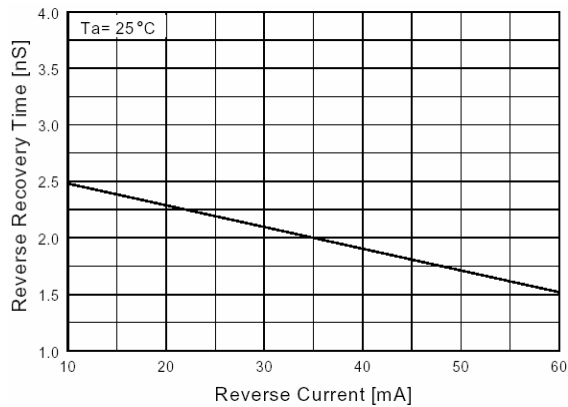


Fig 7. Reverse Recovery Time vs. Reverse Current
TRR - IR 10 to 60mA

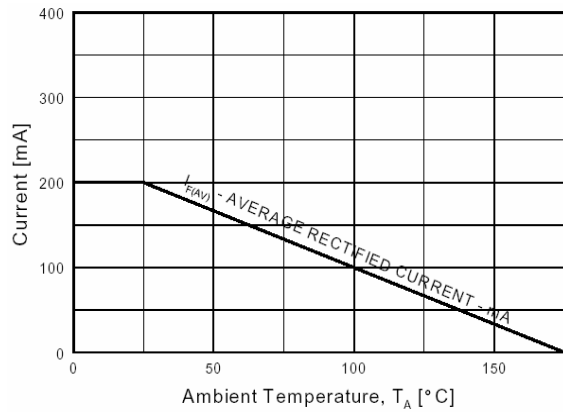


Fig 8. Average Rectified Current ($I_{F(AV)}$)
vs. Ambient Temperature(T_A)

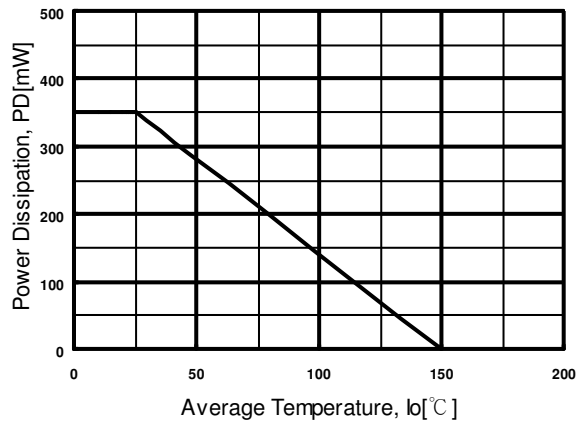


Fig 9. Power Derating Curve

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